27 May 2004

Updated Search

09/831,763

C 1 1-12	<del></del>	Updated search		01/831,76-
L Number	Hits	Search Text	DB	Time stamp
3	1	1997-282330.NRAN.	DERWENT	2004/05/27
				09:03
11	6	6099711.URPN.	USPAT	2004/05/27
			*	09:03
12	2	6099711.URPN. and (iron or fe!)	USPAT;	2004/05/27
			US-PGPUB;	09:06
			EPO; JPO;	, ,
			DERWENT;	
1.			IBM_TDB	
13	6	6099711.URPN.	USPAT	2004/05/27
· ·				09:05
14	1	"5186811".PN.	USPAT	2004/05/27
1			·	09:05
20	767	205/123,157.ccls.	USPAT;	2004/05/27
İ			US-PGPUB;	09:07
			EPO; JPO;	
			DERWENT;	
	·		IBM_TDB	
21	78	205/123,157.ccls. and (iron or fe!)	USPAT;	2004/05/27
			US-PGPUB;	09:20
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
22	59	(205/123,157.ccls. and (iron or fe!)) and (copper or	USPAT;	2004/05/27
		cu!)	US-PGPUB;	09:07
1			EPO; JPO;	05.07
			DERWENT;	
•			IBM_TDB	
23	296	205/101.ccls.	USPAT;	2004/05/27
	`		US-PGPUB;	09:28
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	_
24	86	205/101.ccls. and (iron or fe!)	USPAT;	2004/05/27
			US-PGPUB;	09:28
			EPO; JPO;	
	-		DERWENT;	
			IBM_TDB	
25	13	(205/101.ccls. and (iron or fe!)) and (semiconductor	USPAT;	2004/05/27
]		or silicon)	US-PGPUB;	09:28
'			EPO; JPO;	
	]		DERWENT;	
] [	ŀ		IBM_TDB	
26	203	205/103.ccls.	USPAT;	2004/05/27
·			US-PGPUB;	09:28
	ĺ		EPO; JPO;	
			DERWENT;	
			IBM_TDB	
28	10	(205/103.ccls. and (iron or fel)) and (semiconductor	USPAT;	2004/05/27
		or silicon)	US-PGPUB;	09:32
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
			·	

27	37	205/103.ccls. and (iron or fe!)	LICOAT	2004/05/05
-'	37	203/103.ccis. and (fron or re!)	USPAT;	2004/05/27
			US-PGPUB;	09:30
			EPO; JPO;	
			DERWENT;	
_	1187	205/\$.ccls. and (puls\$3 with current)	IBM_TDB	
	110/	2007 \$.ccis. and (puis\$5 with current)	USPAT;	2003/06/11 14:51
	1		US-PGPUB;	
1			EPO; JPO;	
			DERWENT;	
_	566	(205/d calc and (a lada and	IBM_TDB	
-	500	(205/\$.ccls. and (puls\$3 with current)) and copper	USPAT;	2003/06/11
			US-PGPUB;	14:50
1			EPO; JPO;	
			DERWENT;	
	1222	205/6 1 1/ 1 62 11/	IBW_TDB	
-	1232	205/\$.ccls. and (puls\$3 with (current or revers\$3))	USPAT;	2003/06/11 14:51
			US-PGPUB;	
			EPO; JPO;	
		·	DERWENT;	
	012/	205 (\$ 1	IBW_TDB	
_	8136	205/\$.ccls. and copper	USPAT;	2003/06/11
			U5-PGPUB;	14:52
			EPO; JPO;	
			DERWENT;	
	0.470	205.4	IBM_TDB	
-	2472	205/\$.ccls. and semiconductor	USPAT;	2003/06/11
			US-PGPUB;	14:52
			EPO; JPO;	
			DERWENT;	
	100	(005/4-1	IBM_TDB	
_	189	(205/\$.ccls. and (puls\$3 with (current or revers\$3)))	USPAT;	2003/06/11
		and (205/\$.ccls. and copper) and (205/\$.ccls. and	US-PGPUB;	14:52
*		semiconductor)	EPO; JPO;	
			DERWENT;	
:	150	//00F/h	IBW_TDB	
-	150	((205/\$.ccls. and (puls\$3 with (current or	USPAT;	2003/06/11 15:01
		revers\$3))) and (205/\$.ccis. and copper) and	US-PGPUB;	
	. 1	(205/\$.ccls. and semiconductor)) and (recess or	EPO; JPO;	
		trench or via or hole)	DERWENT;	
		(//205/4 1 1 1 / 1 4 5 2 2 2 2	IBW_TDB	
-	22	(((205/\$.ccls. and (puls\$3 with (current or	USPAT;	2003/06/12
		revers\$3))) and (205/\$.ccls. and copper) and	US-PGPUB;	09:20
		(205/\$.ccls. and semiconductor)) and (recess or	EPO; JPO;	•
	ĺ	trench or via or hole)) and ((inert or noble or	DERWENT;	
		titanium) near (anode or electrode or	IBW_TDB	
_		counterelectrode))		
-	2	"6432293"	USPAT;	2003/06/11
			US-PGPUB;	15:24
			EPO; JPO;	
			DERWENT;	
_		2000 (4250) ND 4N	IBM_TDB	
	1	2000-642506.NRAN.	DERWENT	2003/06/11
				15:22

	1	1005/4 1 11	T	
-	61	205/\$.ccls. and damascene and puls\$5	USPAT;	2003/06/11
	1		US-PGPUB;	16:06
			EPO; JPO;	
		i.	DERWENT;	
-			IBW_TDB	
<b> </b>	258	205/\$.ccls. and ((cathodic or plating or forward) adj	USPAT;	2003/06/11
		(current or pulse)) and ((anodic or polishing or	U5-PGPUB;	16:09
		etching or dissolution) adj (current or pulse))	EPO; JPO;	
			DERWENT;	
	]		IBM_TDB	
-	43	(205/\$.ccls. and ((cathodic or plating or forward) adj	USPAT;	2003/06/11
		(current or pulse)) and ((anodic or polishing or	US-PGPUB;	16:09
		etching or dissolution) adj (current or pulse))) and	EPO; JPO;	
		semiconductor	DERWENT;	
			IBM_TDB	
-	, 2	gb-2214520-\$.did.	USPAT;	2003/06/12
			US-PGPUB;	08:47
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	35091	205/\$.ccls.	USPAT;	2003/06/12
	333,1	4.55.5.	US-PGPUB;	09:03
			EPO; JPO;	09.03
			DERWENT;	
			IBM_TDB	
_	2587	205/\$.ccls. and (semiconductor or (silicon adj	USPAT;	2003/06/12
	2507	wafer))	US-PGPUB;	
		Waj Gi //	1	09:19
			EPO; JPO;	
		·	DERWENT;	
_	1589	(205/\$ cold and (comissandusters on (ciliary all	IBM_TDB	2002/07/42
-	1009	(205/\$.ccls. and (semiconductor or (silicon adj	USPAT;	2003/06/12
		wafer))) and (recess or trench or via or hole)	US-PGPUB;	09:20
			EPO; JPO;	
			DERWENT;	
	010	//205/\$ and and (a	IBM_TDB	0000/5/45
-	918	((205/\$.ccls. and (semiconductor or (silicon adj	USPAT;	2003/06/12
		wafer))) and (recess or trench or via or hole)) and	US-PGPUB;	09:20
		copper	EPO; JPO;	
			DERWENT;	
		//or/h	IBM_TDB	
-	286	((205/\$.ccls. and (semiconductor or (silicon adj	USPAT;	2003/06/12
		wafer))) and (recess or trench or via or hole)) and	US-PGPUB;	09:31
		(copper near (electroplat\$4 or electrochem\$6 or	EPO; JPO;	
		electroly\$6))	DERWENT:	
		///	IBW_TDB	
-	48	(((205/\$.ccls. and (semiconductor or (silicon adj	USPAT;	2003/06/12
		wafer))) and (recess or trench or via or hole)) and	US-PGPUB;	09:31
		(copper near (electroplat\$4 or electrochem\$6 or	EPO; JPO;	
		electroly\$6))) and (iron or "fe(II)" or "fe(III)" or fe!	DERWENT;	
		or ((ferric or ferrous) adj ion))	IBM_TDB	

i _	336	(205/\$.ccls. and (semiconductor or (silicon adj	USPAT;	2003/06/12
	330	wafer))) and (copper near (electroplat\$4 or	US-PGPUB;	09:31
		electrochem\$6 or electroly\$6))	EPO; JPO;	07.51
		Classification of electroly 40))	DERWENT;	
			IBM_TDB	
l _	63	((205/\$.ccls. and (semiconductor or (silicon adj	USPAT;	2003/06/12
-	03	wafer))) and (copper near (electroplat\$4 or	US-PGPUB;	09:31
		electrochem\$6 or electroly\$6))) and (iron or "fe(II)"	EPO; JPO;	09.51
· ]		or "fe(III)" or fe! or ((ferric or ferrous) adj ion))	DERWENT;	
		or rectiff or record (terric or remods) adjustiff		
	15	(((205/\$.ccls. and (semiconductor or (silicon adj	IBM_TDB USPAT;	2002/0//12
-	15	'''	1	2003/06/12
		wafer))) and (copper near (electroplat\$4 or	US-PGPUB;	09:34
		electrochem\$6 or electroly\$6))) and (iron or "fe(II)"	EPO; JPO;	
		or "fe(III)" or fe! or ((ferric or ferrous) adj ion)))	DERWENT;	
		not ((((205/\$.ccls. and (semiconductor or (silicon adj	IBW_TDB	
		wafer))) and (recess or trench or via or hole)) and		
		(copper near (electroplat\$4 or electrochem\$6 or		
		electroly\$6))) and (iron or "fe(II)" or "fe(III)" or fe!		
	700	or ((ferric or ferrous) adj ion)))	1100.7	0000 (0) (1)
-	782	205/291-298.ccls.	USPAT;	2003/06/12
			US-PGPUB;	09:34
		•	EPO; JPO;	
			DERWENT;	·
.	440		IBW_TDB	
· .	118	205/291-298.ccls. and (iron or fe! or ferrous or	USPAT;	2003/06/12
		ferric)	US-PGPUB;	09:34
			EPO; JPO;	
			DERWENT;	
	404		IBM_TDB	
-	106	205/291-298.ccls. and (semiconductor or silicon)	USPAT;	2003/06/12
			US-PGPUB;	09:35
			EPO; JPO;	
i			DERWENT;	
		<b></b>	IBW_LDB	
-	28	(205/291-298.ccls. and (iron or fel or ferrous or	USPAT;	2003/06/12
		ferric)) and (205/291-298.ccls. and (semiconductor	US-PGPUB;	09:37
		or silicon))	EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	2	6099711.pn.	USPAT;	2003/06/12
			US-PGPUB;	09:38
			EPO; JPO;	
			DERWENT;	
	ļ		IBW_TDB	
-	9	"6099711"	USPAT;	2003/06/12
		·	US-PGPUB;	09:38
			EPO; JPO;	
			DERWENT;	
			IBW_TDB	
-	1	1997-282330.NRAN.	DERWENT	2003/06/12
				09:38

_	3205	205/101,102,103,104,118,122,123,157,183,220,221,291	2025047	2003/06/12
	3209	203/101,102,103,104,110,122,123,137,103,220,221,231	US-PGPUB;	10:50
		•	EPO; JPO;	10:50
			DERWENT;	
	· ·		IBM_TDB	
	505	205/101,102,103,104,118,122,123,157,183,220,221,291		2002/06/12
-	505	and semiconductor and (recess or trench or via or	US-PGPUB;	2003/06/12 10:51
		hole)	EPO; JPO;	10.51
		noie)	DERWENT;	
			IBM_TDB	
_	549	205/101,102,103,104,118,122,123,157,183,220,221,291		2003/06/12
	377	and semiconductor and (recess or trench or via or	US-PGPUB;	10:51
		hole or opening)	EPO; JPO;	10.51
		note of opening)	DERWENT;	
			IBM_TDB	
_	391	(205/101,102,103,104,118,122,123,157,183,220,221,291		2003/04/12
	371	and semiconductor and (recess or trench or via or	US-PGPUB;	2003/06/12 10:51
		hole or opening)) and copper	EPO; JPO;	10.51
		note of opening), and copper	DERWENT;	
			IBM_TDB	
_	220	((205/101,102,103,104,118,122,123,157,183,220,221,29	1	2003/06/12
	220	and semiconductor and (recess or trench or via or	US-PGPUB;	10:52
		hole or opening)) and copper) and ((seed or barrier)	EPO; JPO;	10.52
		near layer)	DERWENT;	
		TIOM MYCI )	IBM_TDB	
	69	   (((205/101,102,103,104,118,122,123,157,183,220,221,29		2003/06/12
		and semiconductor and (recess or trench or via or	US-PGPUB;	10:52
		hole or opening)) and copper) and ((seed or barrier)	EPO; JPO;	10.32
		near layer)) and puls\$3	DERWENT;	
			IBM_TDB	
_	69	(((205/101,102,103,104,118,122,123,157,183,220,221,29		2003/06/12
		and semiconductor and (recess or trench or via or	US-PGPUB;	12:06
		hole or opening)) and copper) and ((seed or barrier)	EPO; JPO;	16.00
		near layer)) and puls\$5	DERWENT;	
		A series of the	IBM_TDB	
_	44	((((205/101,102,103,104,118,122,123,157,183,220,221,2		2003/06/12
	- 1	and semiconductor and (recess or trench or via or	US-PGPUB;	12:09
		hole or opening)) and copper) and ((seed or barrier)	EPO; JPO;	
		near layer)) and puls\$5) and ((semiconductor or	DERWENT;	
		silicon) with (circuit))	IBM_TDB	
-	, 9	((((205/101,102,103,104,118,122,123,157,183,220,221,2		2003/06/12
,		and semiconductor and (recess or trench or via or	US-PGPUB;	14:18
		hole or opening)) and copper) and ((seed or barrier)	EPO; JPO;	
		near layer)) and puls\$5) and ((semiconductor or	DERWENT;	
		silicon) with (circuit adj board))	IBM_TDB	
- '	1	de-4344387-a1.did.	USPAT;	2003/06/12
			US-PGPUB;	14:22
			EPO; JPO;	
•		•	DERWENT;	
i			IBM_TDB	
-	1	1995-232640.NRAN.	DERWENT	2003/06/12
		•		14:20

			<del></del>	· · · · · · · · · · · · · · · · · · ·
-	9	"5976341"	USPAT;	2003/06/12
			US-PGPUB;	14:22
İ			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	0	1997wo-de19206.ap,prai.	USPAT;	2004/01/14
			US-PGPUB;	09:17
		,	EPO; JPO;	
			DERWENT;	
			IBM_TDB	ı.
-	2	6099711.pn.	USPAT;	2004/01/14
			US-PGPUB;	09:24
		•	EPO; JPO;	
		•	DERWENT;	
			IBW_TDB	
-	1	1997-282330.NRAN.	DERWENT	2004/01/14
				09:18
-	2	5893966.pn.	USPAT;	2004/01/14
			US-PGPUB;	09:24
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
- '	1	5893966.pn. and (semiconductor with circuit)	USPAT;	2004/01/14
	ļ		US-PGPUB;	09:24
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	